



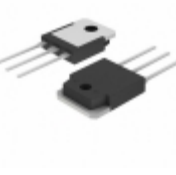
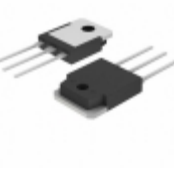

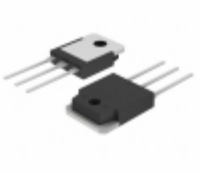
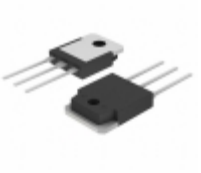

	GP2M020A050H	
	Hersteller-Teilenummer:	GP2M020A050H
	Hersteller / Marke:	Global Power Technologies Group
	Teil der Beschreibung:	MOSFET N-CH 500V 18A TO220
	Datenblätter:	 GP2M020A050H.pdf
	RoHs Status:	Bleifrei / RoHS-konform
	Lagerzustand:	New original, 1900 pcs Stock Available.
	Liefern von:	Hong Kong
	Versandweg:	DHL/Fedex/TNT/UPS/EMS
Image may be representation. See specs for product details.		

Spezifikationen

Teilenummer	GP2M020A050H
Hersteller	Global Power Technologies Group
Beschreibung	MOSFET N-CH 500V 18A TO220
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	1900 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-220-3
Supplier Device-Gehäuse	TO-220
Verlustleistung (max)	290W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	500V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	18A (Tc)
Rds On (Max) @ Id, Vgs	300 mOhm @ 9A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	44nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	2880pF @ 25V
Verpackung	Tube

GP2M020A050H ist neu im Original, Suche GP2M020A050H Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie GP2M020A050H Global Power Technologies Group mit Garantie und Vertrauen. Anfrage GP2M020A050H: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>GP2M020A050F Global Power Technologies Group MOSFET N-CH 500V 18A TO220F</p>	 <p>GP2M012A060H Global Power Technologies Group MOSFET N-CH 600V 12A TO220</p>	 <p>GP2M023A050N Global Power Technologies Group MOSFET N-CH 500V 23A TO3PN</p>	 <p>GP2M020A060N Global Power Technologies Group MOSFET N-CH 600V 20A TO3PN</p>
 <p>GP2S+ MINI MINI QFN</p>	 <p>GP2M020A050N Global Power Technologies Group MOSFET N-CH 500V 20A TO3PN</p>	 <p>GP2M012A080NG Global Power Technologies Group MOSFET N-CH 800V 12A TO3PN</p>	 <p>GP2M013A050F Global Power Technologies Group MOSFET N-CH 500V 13A TO220F</p>

heiße Teile

Mehr

⊗ GP2A25NJ	↔ GP2A28A1J00F	⇒ GP2A28N1J00F	D GP2AP002A00F	↔ GP2AP002S00F
⊥ GP2AP003A10F	⊗ GP2AP007A00F	D GP2AP008T00F	⇒ GP2AP030A00F	↔ GP2AP052A00F
⊗ GP2AP052A00F	⊥ GP2L26K2	⊗ GP2M002A060FG	↔ GP2M004A060PG	↔ GP2M004A065FG
D GP2M004A065PG	⊗ GP2M005A050PG	⊥ GP2M005A060CG	⊗ GP2M005A060FG	↔ GP2M005A060PGH
⇒ GP2M008A060FGH	↔ GP2M010A060F	⊗ GP2M010A065F	⊥ GP2M011A090NG	↔ GP2M012A080NG
↔ GP2M020A060N	⇒ GP2S24J0000F	D GP2S27T3	⊗ GP2S27T3J00F	⊥ GP2S27V6
⊗ GP2S29SVJ00F	D GP2S40JJ000F	⇒ GP2S700HCP	↔ GP2S700HCP	↔ GP2W0004YP
⊥ GP2W0110YPS	⊗ GP2W0112YPOF	↔ GP2W0118YPS	⇒ GP2W0150YP0F	↔ GP2W3104XP0F
⊗ GP2W3104YP0F	⊥ GP2W3106YP0F	⊗ GP2W3152YP0F	D GP2W3172XP0F	↔ GP2W3270XP0F
↔ GP2Y0A02YK0F	⊗ GP2Y0A02YK0F	⊥ GP2Y0A21	⊗ GP2Y0A21YK0F	↔ GP2Y0A41SK0F

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